Transistors

4V Drive Pch MOSFET **RSR025P03**

Structure

Silicon P-channel MOSFET

Features

- 1) Low On-resistance
- 2) Space saving-small surface mount package (TSMT3)
- 3) 4V drive

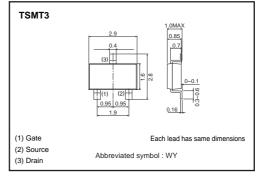
Applications

Switching

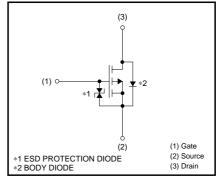
Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RSR025P03		0	

•Dimensions (Unit : mm)



Inner circuit



Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	-30	V
Gate-source voltage		Vgss	±20	V
Droin ourrant	Continuous	ID	±2.5	А
Drain current	Pulsed	I _{DP} *1	±10	А
Source current	Continuous	ls	-0.8	А
(Body diode)	Pulsed	Isp *1	-10	А
Total power dissipation		P _D *2	1	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W

* Mounted on a ceramic board



1/4

Transistors

•Electrical characteristics (Ta=25°C)

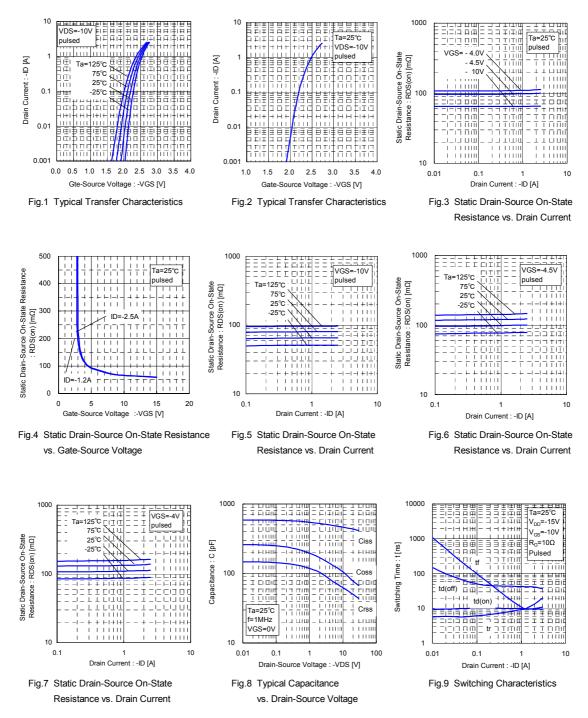
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	-30	-	_	V	I _D = -1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	-1	μΑ	V_{DS} = -30V, V_{GS} =0V
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$
Static drain-source on-state resistance		_	70	98	mΩ	I _D = -2.5A, V _{GS} = -10V
	$R_{DS(on)^*}$	-	100	140	mΩ	I _D = -1.2A, V _{GS} = -4.5V
		-	115	160	mΩ	I _D = -1.2A, V _{GS} = -4V
Forward transfer admittance	Y _{fs} *	1.6	-	_	S	$V_{DS} = -10V, I_{D} = -1.2A$
Input capacitance	Ciss	_	460	_	pF	V _{DS} =-10V
Output capacitance	Coss	-	105	-	рF	Vgs=0V
Reverse transfer capacitance	Crss	-	65	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	10	-	ns	Vdd≒-15V
Rise time	tr *	-	10	-	ns	$I_{D} = -1.2A$
Turn-off delay time	td (off) *	-	42	-	ns	Vgs= –10V R∟=12.5Ω
Fall time	t _f *	-	10	-	ns	$R_{GS}=10\Omega$
Total gate charge	Qg *	-	5.4	-	nC	V _{DD} ≒−15V V _{GS} =−5V
Gate-source charge	Q _{gs} *	-	1.4	-	nC	I _D = –2.5A
Gate-drain charge	Q _{gd} *	-	1.6	-	nC	R∟=6Ω R _G =10Ω

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	-1.2	V	I _S = -0.8A, V _{GS} =0V

Transistors

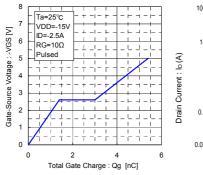
•Electrical characteristic circuits

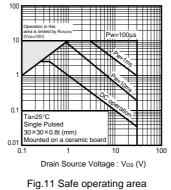


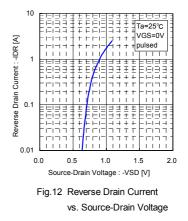
ROHM

RSR025P03

Transistors







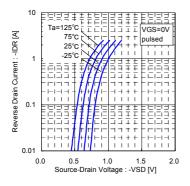


Fig.10 Dynamic Input Characteristics

Fig.13 Reverse Drain Current

vs. Source-Drain Voltage

Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the
 product described in this document are for reference only. Upon actual use, therefore, please request
 that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or
 otherwise dispose of the same, no express or implied right or license to practice or commercially
 exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

It is our top priority to supply products with the utmost quality and reliability. However, there is always a chance of failure due to unexpected factors. Therefore, please take into account the derating characteristics and allow for sufficient safety features, such as extra margin, anti-flammability, and fail-safe measures when designing in order to prevent possible accidents that may result in bodily harm or fire caused by component failure. ROHM cannot be held responsible for any damages arising from the use of the products under conditions out of the range of the specifications or due to non-compliance with the NOTES specified in this catalog.

Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact your nearest sales office.

ROHM Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

www.rohm.com

Contact us : webmaster@rohm.co.jp

Copyright © 2008 ROHM CO.,LTD. ROHM CO., LTD. 21 Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan TEL : +81-75-311-2121 FAX : +81-75-315-0172

Appendix1-Rev2.0

rohm